

# iscN-Channel MOSFET Transistor

## **IRFI510G**

### • FEATURES

• Low drain-source on-resistance: R<sub>DS</sub>(ON) =0.54Ω (MAX)

Enhancement mode:
Vth = 2 to 4V (VDS = 10 V, ID=0.25mA)

- · 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



Switching Voltage Regulators

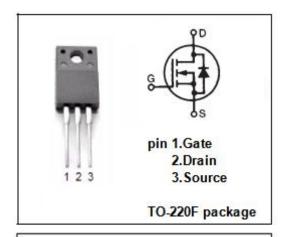


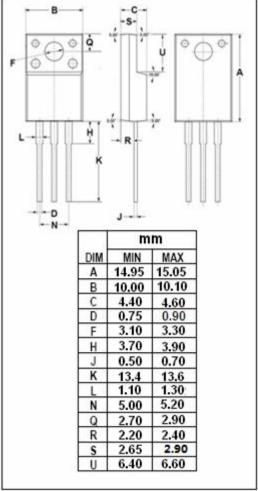
ABSOLUTE MAXIMUM RATINGS(T<sub>a</sub>=25°C)

| ABOOLOTE MAXIMOM (ATMOO(Ta-200) |   |       |            |  |  |  |  |
|---------------------------------|---|-------|------------|--|--|--|--|
| SYMBOL                          | PARAMETER                                   | VALUE | UNIT       |  |  |  |  |
| V <sub>DSS</sub>                | Drain-Source Voltage                        | 100   | V          |  |  |  |  |
| V <sub>GS</sub>                 | Gate-Source Voltage                         | ±20   | V          |  |  |  |  |
| I <sub>D</sub>                  | Drain Current-Continuous                    |       | А          |  |  |  |  |
| I <sub>DM</sub>                 | Drain Current-Single Pulsed 18              |       | А          |  |  |  |  |
| P <sub>D</sub>                  | Total Dissipation @Tc=25°C                  | 27    |            |  |  |  |  |
| Tj                              | Max. Operating Junction Temperature -55~150 |       | $^{\circ}$ |  |  |  |  |
| T <sub>stg</sub>                | Storage Temperature -55~150                 |       | $^{\circ}$ |  |  |  |  |

## • THERMAL CHARACTERISTICS

| SYMBOL    | PARAMETER                          | MAX | UNIT |
|-----------|------------------------------------|-----|------|
| Rth(ch-c) | Channel-to-case thermal resistance | 5.5 | °C/W |







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### **ELECTRICAL CHARACTERISTICS**

Tc=25℃ unless otherwise specified

| SYMBOL              | PARAMETER                      | CONDITIONS   | MIN | ТҮР | MAX       | UNIT       |
|---------------------|--------------------------------|--|-----|-----|-----------|------------|
| BV <sub>DSS</sub>   | Drain-Source Breakdown Voltage | V <sub>GS</sub> =0V; I <sub>D</sub> = 0.25mA   | 100 |     |           | V          |
| V <sub>GS(th)</sub> | Gate Threshold Voltage         | V <sub>DS</sub> = 10V; I <sub>D</sub> =0.25mA  | 2   |     | 4         | V          |
| R <sub>DS(on)</sub> | Drain-Source On-Resistance     | V <sub>GS</sub> =10V; I <sub>D</sub> =2.7A   |     |     | 0.54      | Ω          |
| lgss                | Gate-Source Leakage Current    | V <sub>GS</sub> = ±20V;V <sub>DS</sub> = 0V  |     |     | ±100      | nA         |
| I <sub>DSS</sub>    | Drain-Source Leakage Current   | V <sub>DS</sub> =100V; V <sub>GS</sub> = 0V<br>V <sub>DS</sub> =80V; V <sub>GS</sub> = 0V;T <sub>J</sub> =125℃ |     |     | 25<br>250 | μ <b>A</b> |
| V <sub>SDF</sub>    | Diode forward voltage          | I <sub>DR</sub> =4.5A, V <sub>GS</sub> = 0 V   |     |     | 2.5       | V          |

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